

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT10J312, GT10J312(SM)

HIGH POWER SWITCHING APPLICATIONS
MOTOR CONTROL APPLICATIONS

- Third-generation IGBT
- Enhancement mode type
- High speed : $t_f = 0.30\mu s$ (Max.)
- Low saturation voltage : $V_{CE(sat)} = 2.7V$ (Max.)
- FRD included between emitter and collector

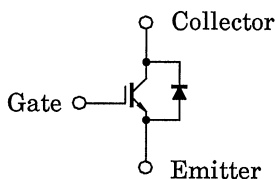
Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	600	V
Gate-Emitter Voltage	V_{GES}	±20	V
Collector Current	DC	I_C	10 A
	1ms	I_{CP}	20 A
Emitter-Collector Forward Current	DC	I_F	10 A
	1ms	I_{FM}	20 A
Collector Power Dissipation (Tc = 25°C)	P_C	60	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

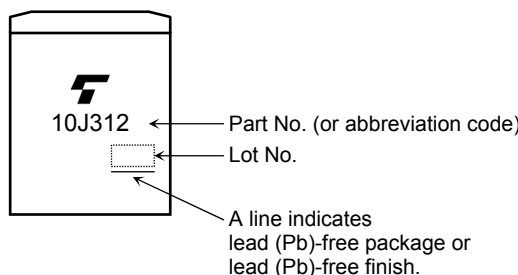
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

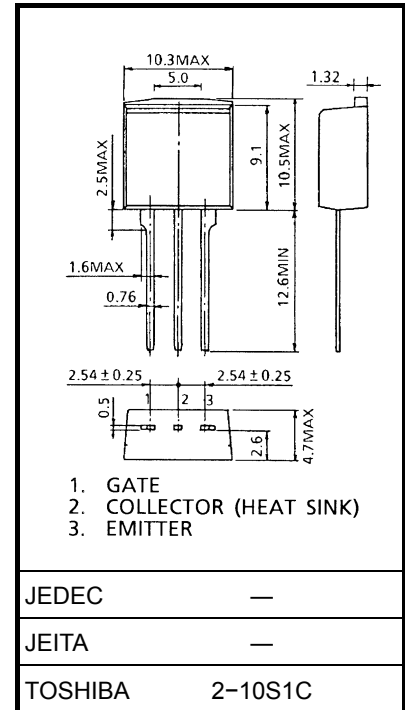
Equivalent Circuit



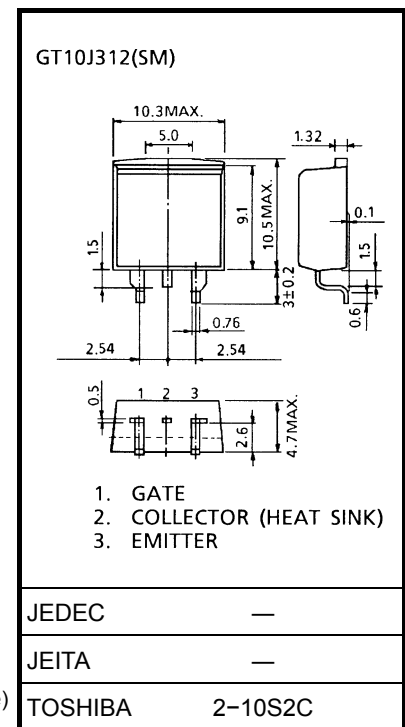
Marking



Unit: mm



Weight: 1.5 g (typ.)

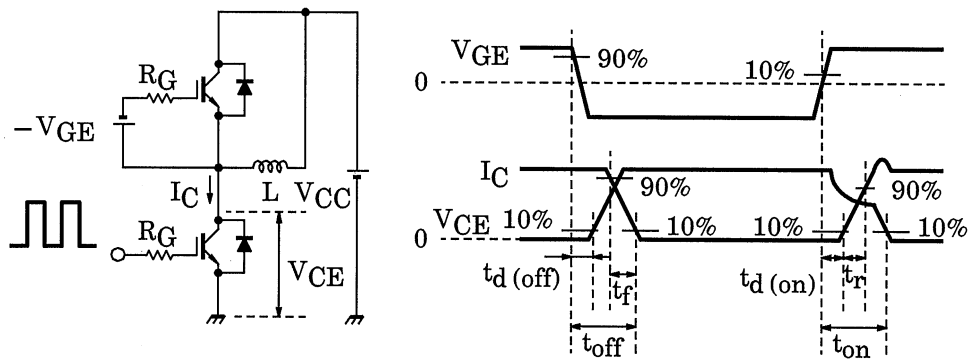


Weight: 1.4 g (typ.)

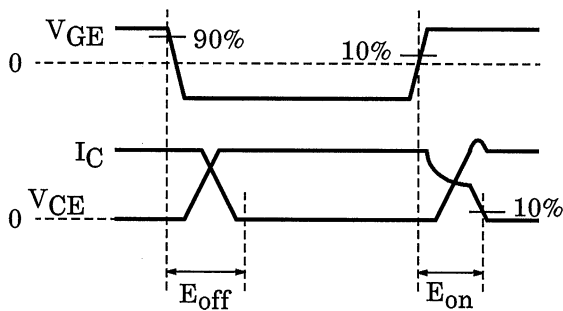
Electrical Characteristics (Ta = 25°C)

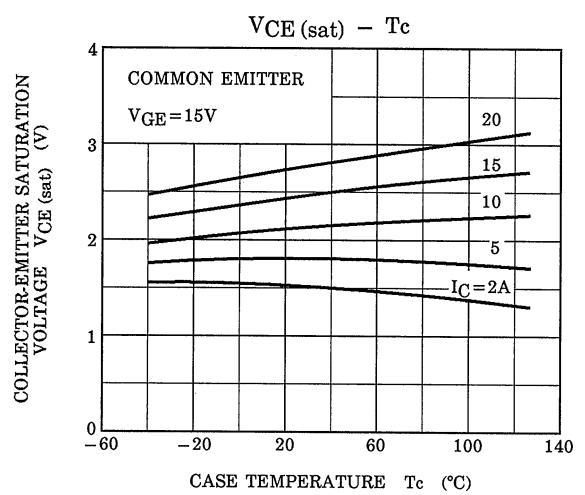
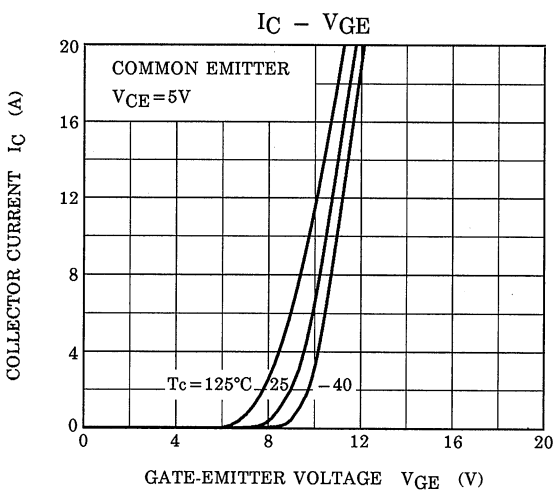
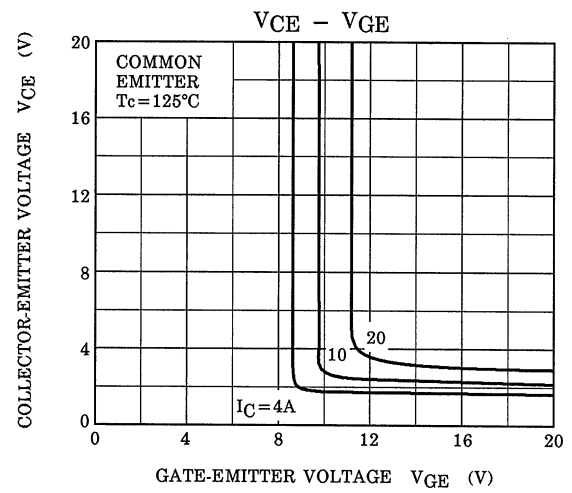
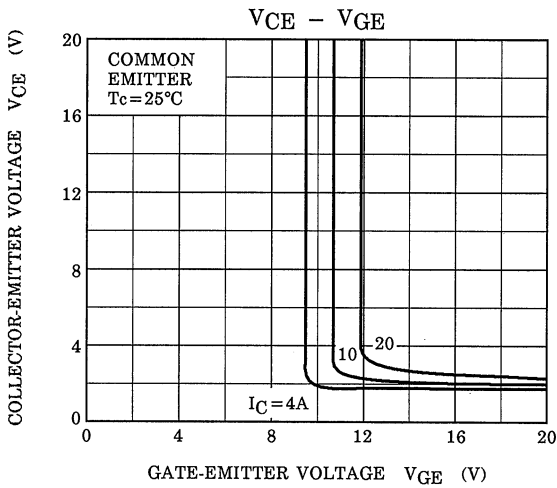
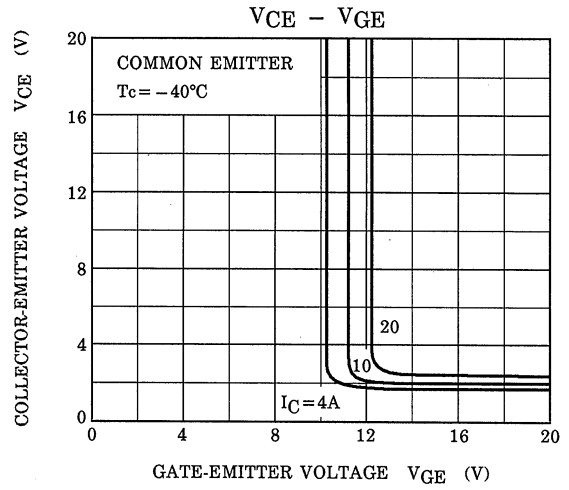
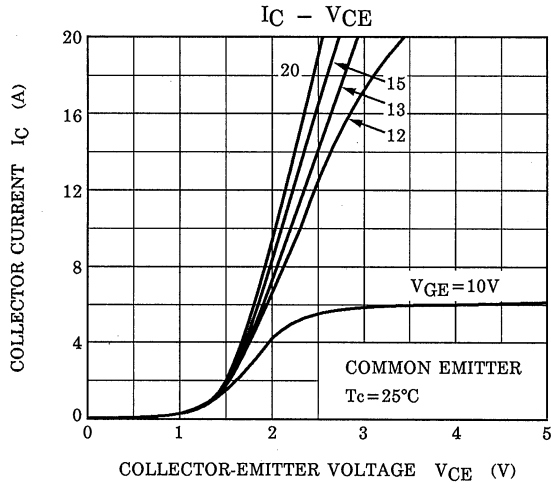
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector Cut-Off Current		I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage		$V_{GE(OFF)}$	$I_C = 1mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 10A, V_{GE} = 15V$	—	2.1	2.7	V
Input Capacitance		C_{ies}	$V_{CE} = 20V, V_{GE} = 0, f = 1MHz$	—	720	—	pF
Switching Time	Rise Time	t_r	Inductive Load $V_{CC} = 300V, I_C = 10A$ $V_{GG} = \pm 15V, R_G = 100\Omega$ (Note 1)	—	0.12	—	μs
	Turn-On Time	t_{on}		—	0.40	—	
	Fall Time	t_f		—	0.15	0.30	
	Turn-Off Time	t_{off}		—	0.40	—	
Peak Forward Voltage		V_F	$I_F = 10A, V_{GE} = 0$	—	—	2.0	V
Reverse Recovery Time		t_{rr}	$I_F = 10A, di/dt = -100A/\mu s$	—	—	200	ns
Thermal Resistance (IGBT)		$R_{th(j-c)}$	—	—	—	2.08	°C/W
Thermal Resistance (Diode)		$R_{th(j-c)}$	—	—	—	3.76	°C/W

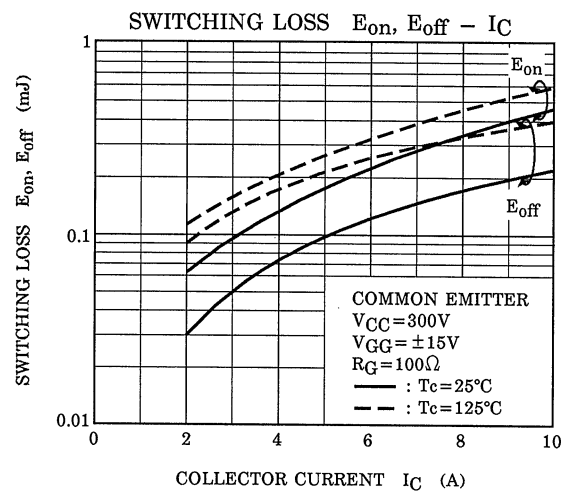
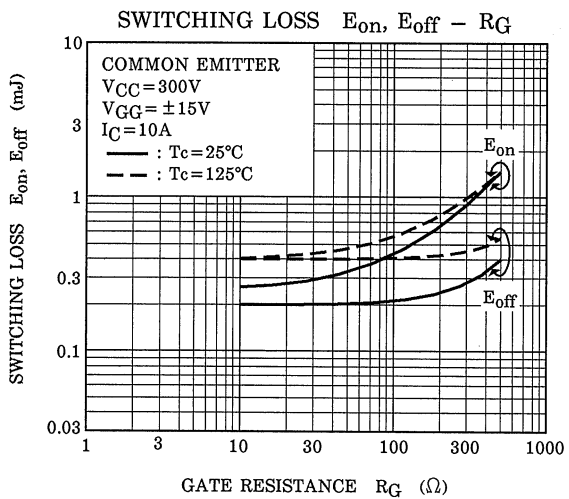
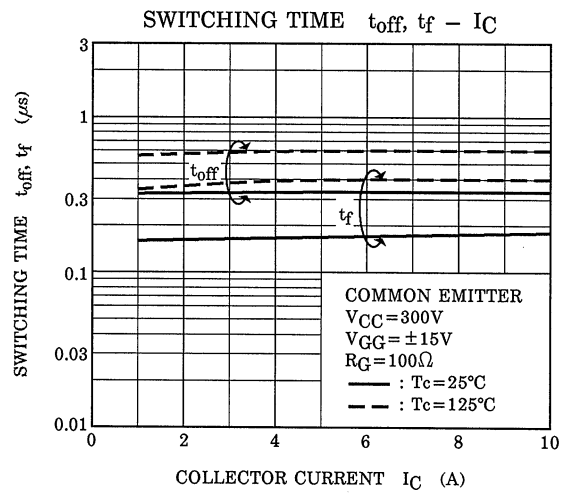
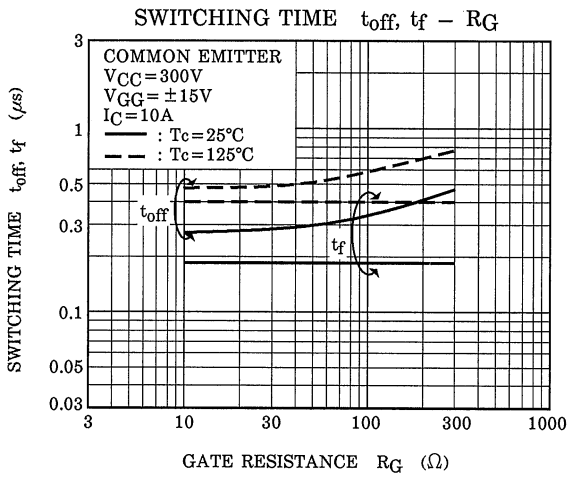
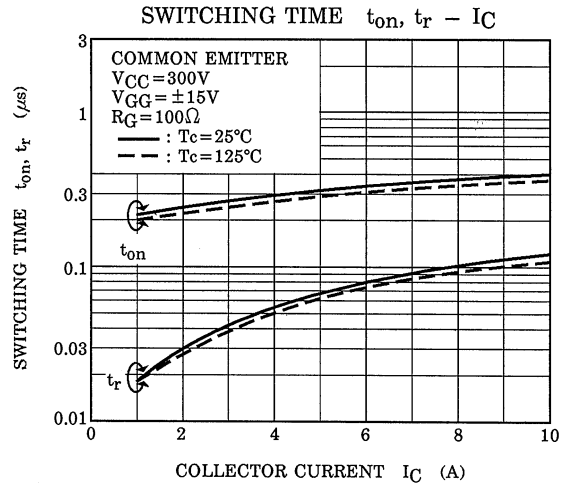
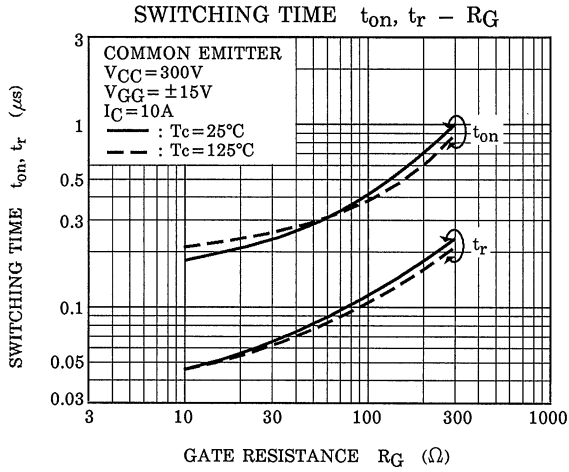
Note 1: Switching time measurement circuit and input / output waveforms

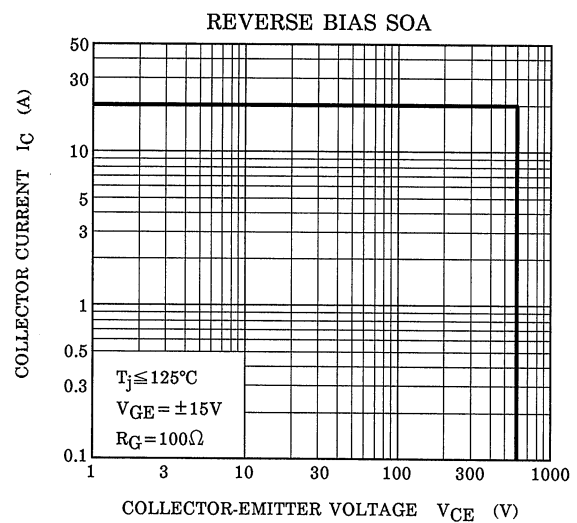
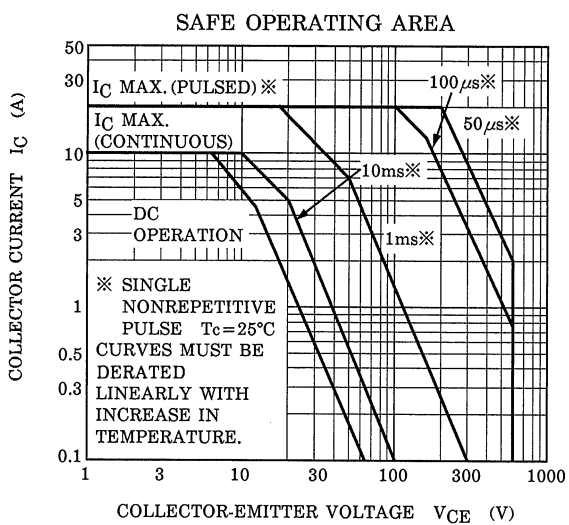
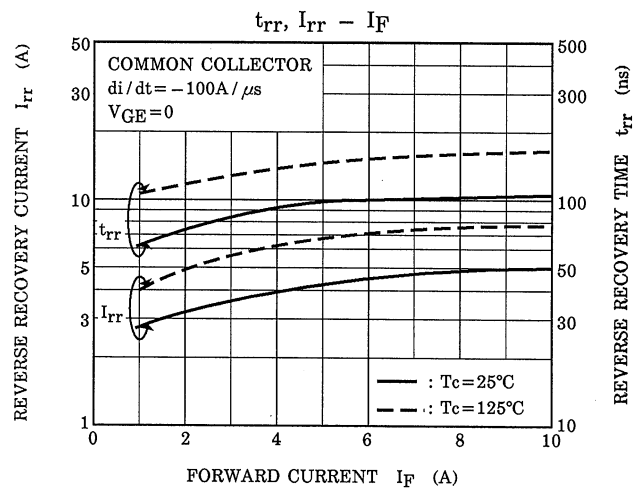
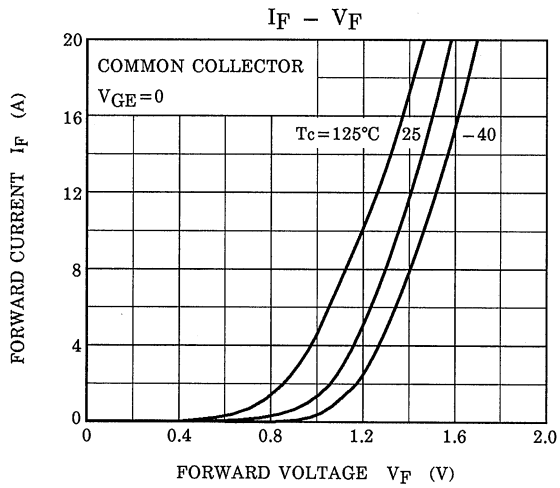
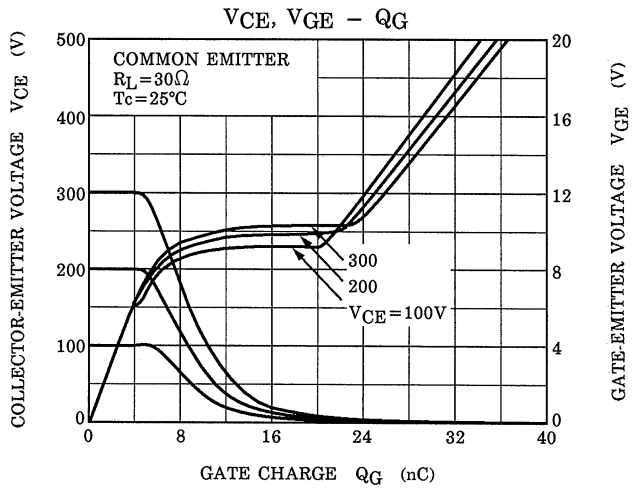
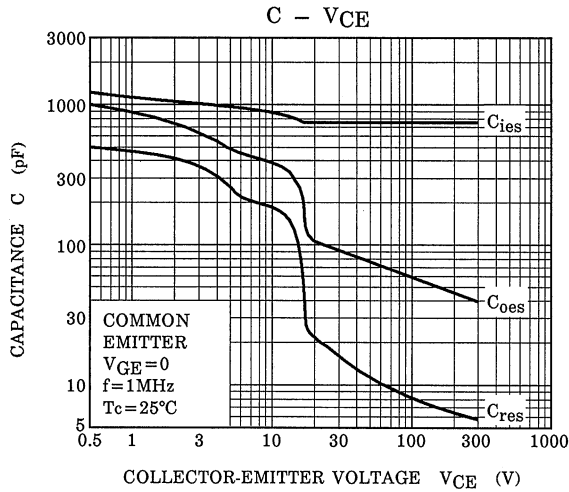


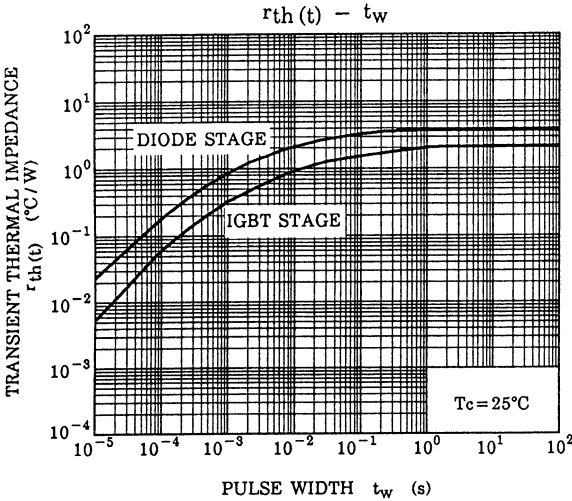
Switching loss measurement waveforms











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